

Cited reference JP 2001-502136

Abstract:

A method is provided for synchronizing a film bulk acoustic resonator (FBAR) positioned on a wafer. The FBAR includes a plurality of layers each having a different thickness. The FBAR indicates at least one of a series resonance and parallel resonance using a frequency which is a function of the thickness of each of at least one layer. A first step of the present invention includes measuring a frequency which indicates, via the FBAR, one of the series resonance and the parallel resonance. The following step includes calculating an amount (A) of the thickness of at least one layer, for which it is necessary to change the thickness in order to minimize the difference between the measured frequency and a reference frequency. The further following step includes changing the at least one layer by the amount (A).